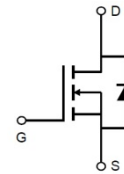
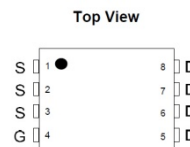
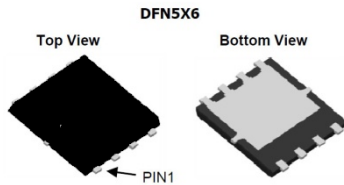


## General Description

N-Channel , 5V Logic Level Control  
 Enhancement mode  
 Very low on-resistance  $R_{DS(on)}$  @  $V_{GS}=4.5\text{ V}$   
 Pb-free lead plating; RoHS compliant

$V_{DS}$	30	V
$R_{DS(on),TYP@VGS=10V}$	4.2	m $\Omega$
$R_{DS(on),TYP@VGS=4.5}$	5.9	m $\Omega$
$I_D$	95	A



Part ID	Package Type	Marking	Tape and reel information
SM95N03A	DFN5x6	95N03	3000PCS/Reel

100% UIS Tested  
 100% Rg Tested

## Maximum ratings, at $T_C = 25^\circ\text{C}$ , unless otherwise specified

Symbol	Parameter	Rating	Unit	
$V_{(RB)DSS}$	Drain-Source breakdown voltage	30	V	
$I_S$	Diode continuous forward current	95	A	
$I_D$	Continuous drain current@ $V_{GS}=10V$	$CT = 25^\circ$	95	A
		$CT = 100^\circ$	70	A
$I_{DM}$	Pulse drain current tested ①	$CT = 25^\circ$	300	A
$E_{AS}$	Avalanche energy, single pulsed ②	450	mJ	
$P_D$	Maximum power dissipation	$CT = 25^\circ$	105	W
$V_{GS}$	Gate-Source voltage	$\pm 20$	V	
$T_{STG} T_J$	Storage and operating temperature range	-55 to 150	$^\circ\text{C}$	

## Thermal Characteristics

Symbol	Parameter	Typical	Unit
R <sub>JC</sub>	Thermal Resistance-Junction to Case	1.1	$^\circ\text{C}/\text{W}$
R <sub>JA</sub>	Thermal Resistance Junction-Ambient	48	$^\circ\text{C}/\text{W}$



## Thermal Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T <sub>j</sub> = 25°C (unless otherwise stated)						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V ID=250μA	30	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current(T <sub>c</sub> =25°C)	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T <sub>c</sub> =125°C)	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	--	--	100	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	--	--	±100	nA
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ,ID=250μA	1.0	1.8	2.5	V
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance ③	V <sub>GS</sub> =10V, ID=30A	--	4.2	5	mΩ
		V <sub>GS</sub> =4.5V, ID=20A	--	4.5	7.5	mΩ
Dynamic Electrical Characteristics @ T <sub>j</sub> = 25°C (unless otherwise stated)						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V, f=1MHz	--	1690	--	pF
C <sub>DSS</sub>	Output Capacitance		--	210	--	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance		--	155	--	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =20V,ID=20A, V <sub>GS</sub> =10V	--	36	--	nC
Q <sub>gs</sub>	Gate-Source Charge		--	11	--	nC
Q <sub>ds</sub>	Gate-Drain Charge		--	16	--	nC
Switching Characteristics						
T <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =20V, ID=10A, R <sub>G</sub> =3.5Ω, V <sub>GS</sub> =10V	--	13	--	nS
t <sub>r</sub>	Turn-on Rise Time		--	15	--	nS
T <sub>d(off)</sub>	Turn-Off Delay Time		--	20	--	nS
t <sub>f</sub>	Turn-Off Fall Time		--	14	--	nS
Source- Drain Diode Characteristics@ T <sub>j</sub> = 25°C (unless otherwise stated)						
V <sub>SD</sub>	Forward on voltage	I <sub>SD</sub> =30A,V <sub>GS</sub> =0V		0.8	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	T <sub>j</sub> =25°C,I <sub>sd</sub> =20A, di/dt=500A/μs		22		nS
Q <sub>rr</sub>	Reverse Recovery Charge			13		nC

### NOTE:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T<sub>Jmax</sub>, starting T<sub>J</sub> = 25°C, L = 0.5mH,R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 43A, V<sub>GS</sub> = 10V. Part not recommended for use above this value
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.

## Typical Characteristics

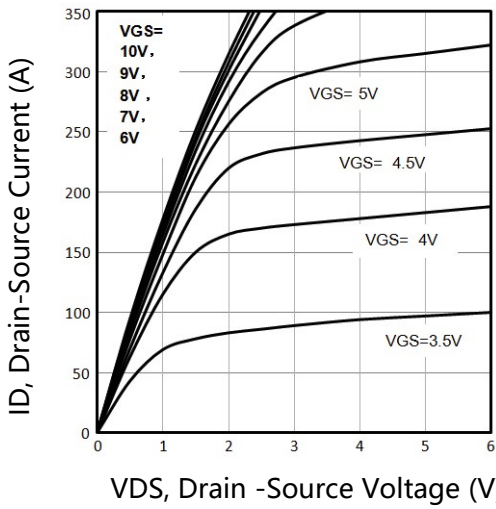


Fig1. Typical Output Characteristics

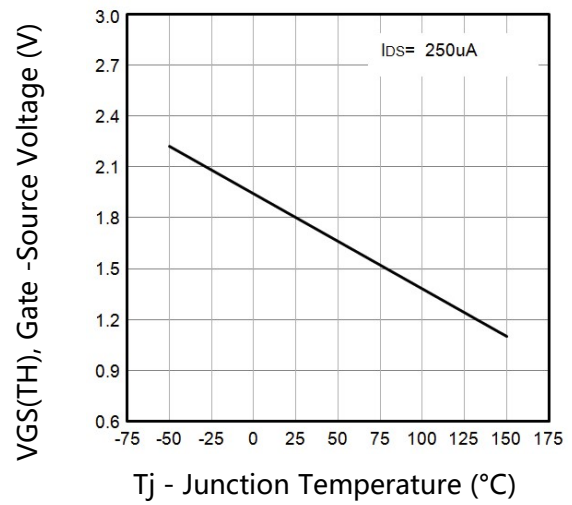


Fig2. VGS(TH) Gate-Source Voltage Vs. Tj

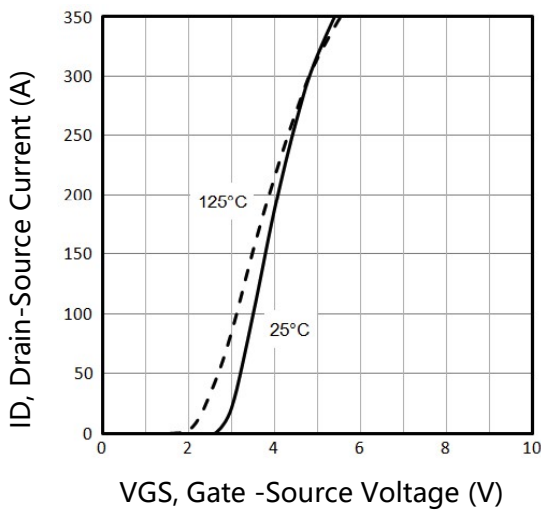


Fig3. Typical Transfer Characteristics

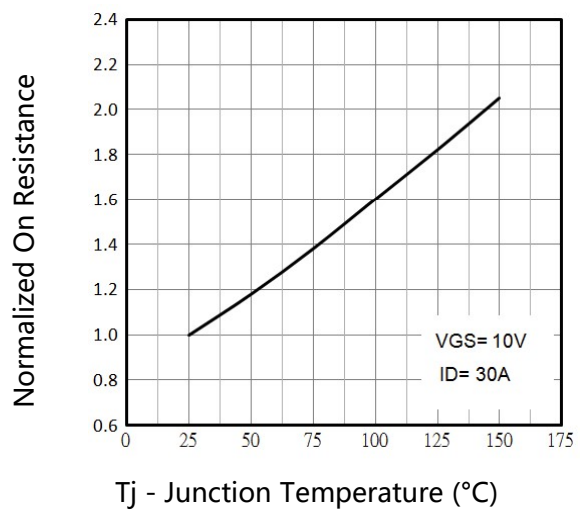


Fig4. Normalized On-Resistance Vs. Tj

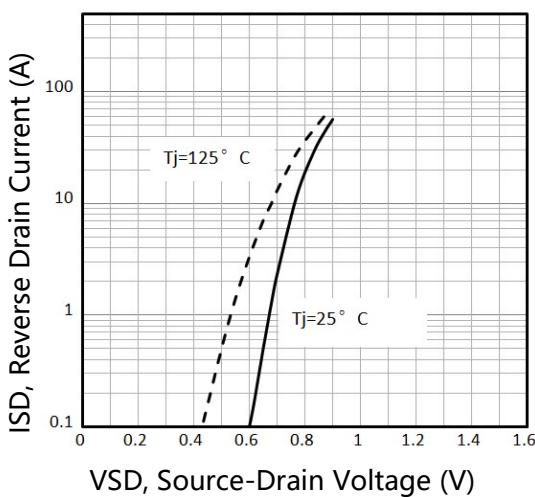


Fig5. Typical Source-Drain Diode Forward Voltage

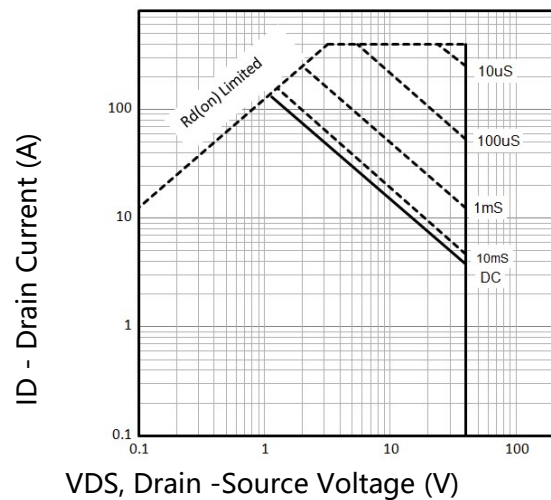


Fig6. Maximum Safe Operating Area

## Typical Characteristics

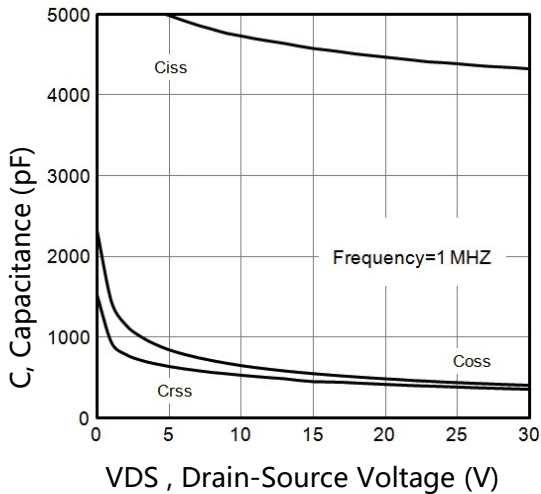


Fig7. Typical Capacitance Vs. Drain-Source Voltage

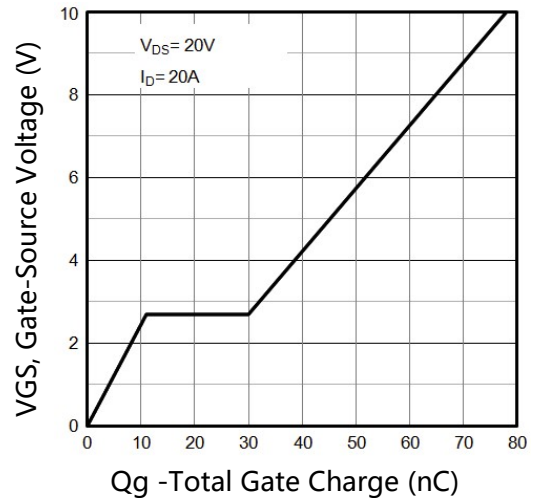


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

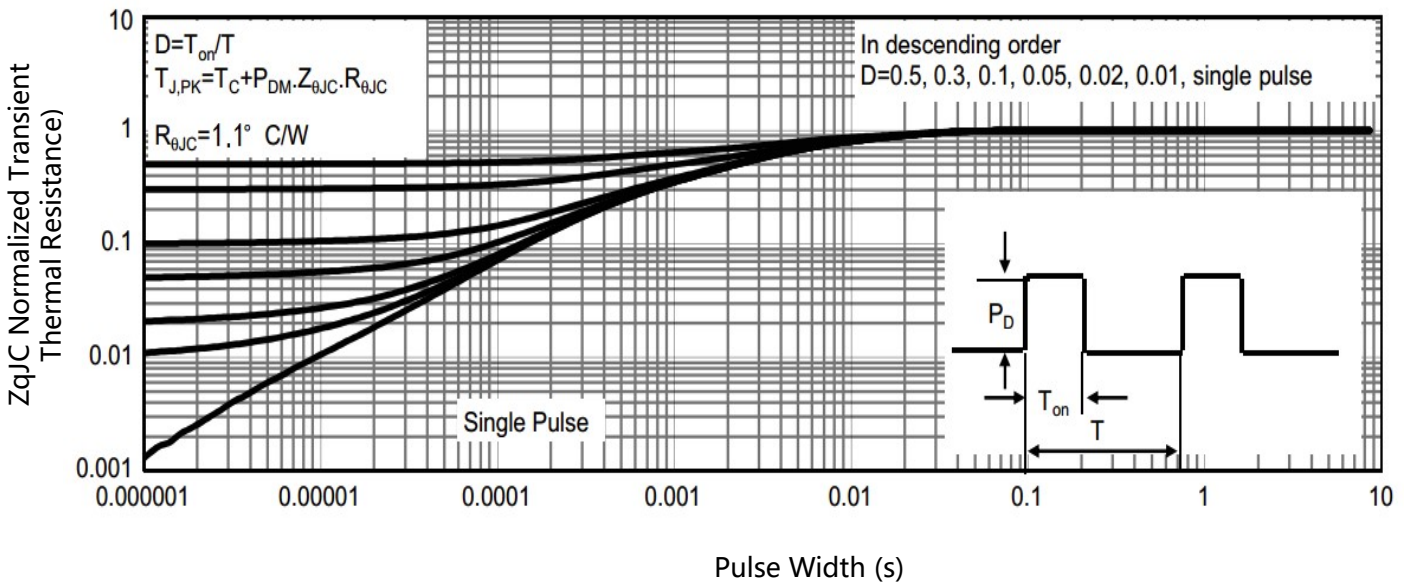


Fig9 . Normalized Maximum Transient Thermal Impedance

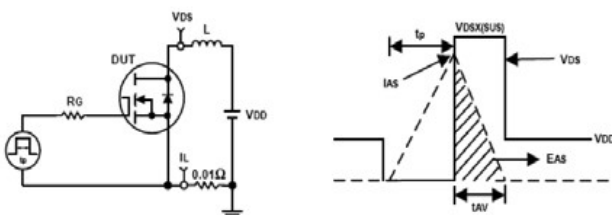


Fig10. Unclamped Inductive Test Circuit and waveforms

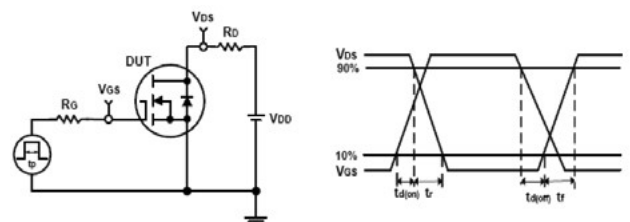
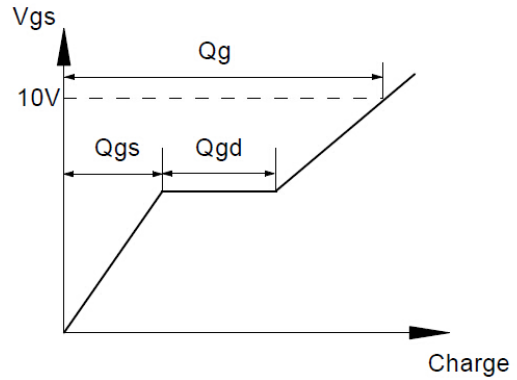
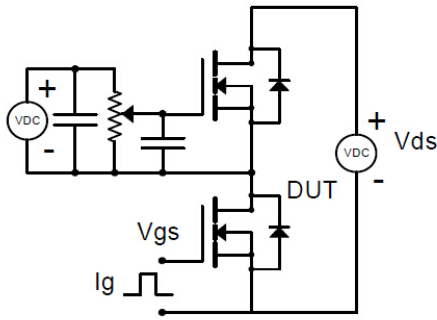
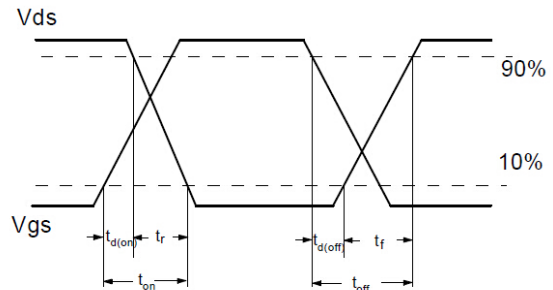
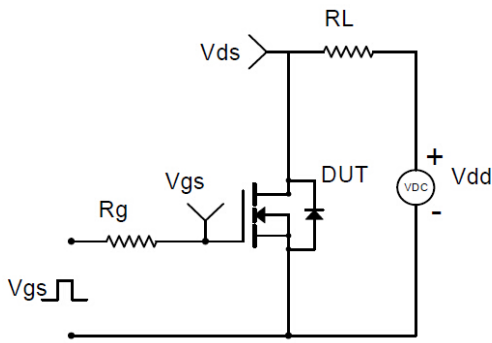


Fig11. Switching Time Test Circuit and waveform:

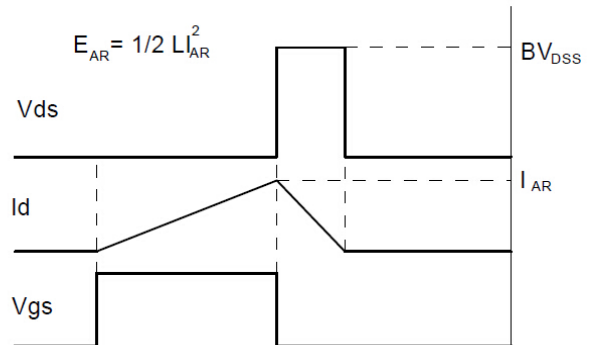
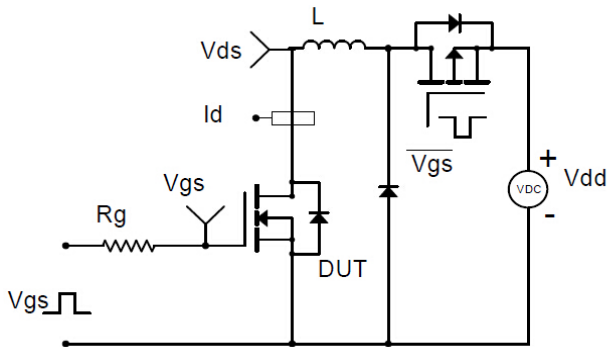
### Gate Charge Test Circuit & Waveform



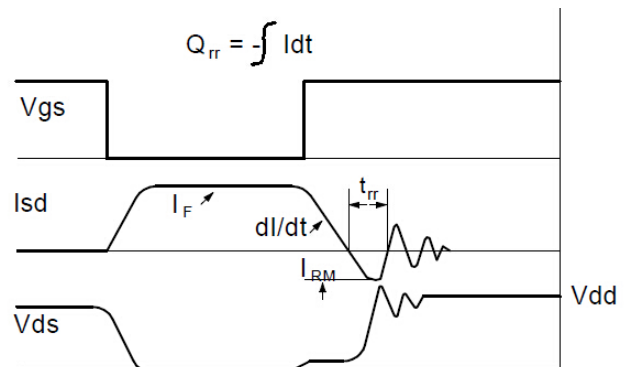
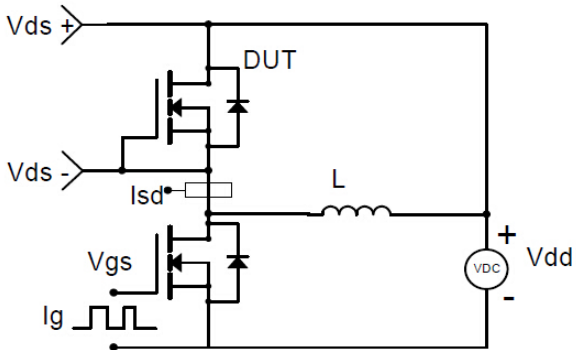
### Resistive Switching Test Circuit & Waveforms



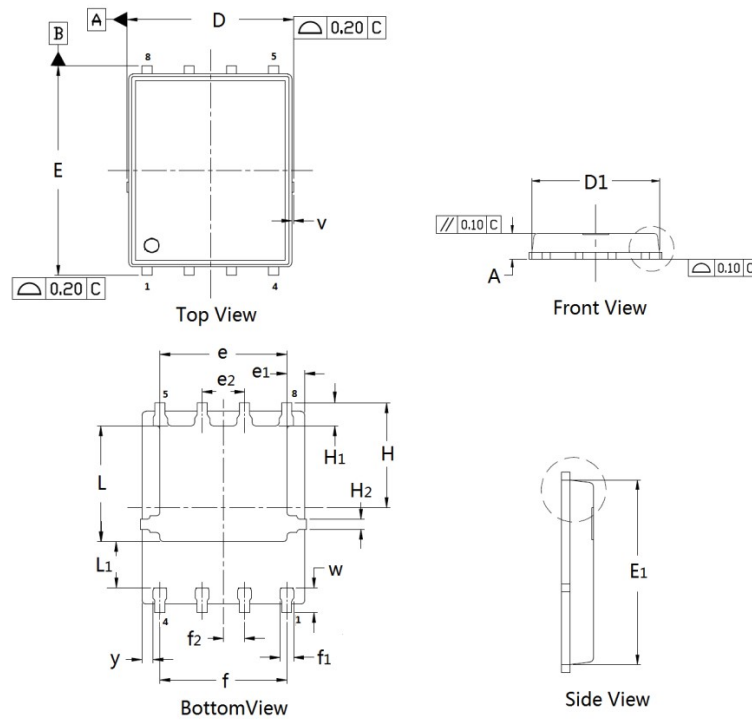
### Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



### Diode Recovery Test Circuit & Waveforms



## DFN5×6 Package Outline Data



### DIMENSIONS ( unit : mm )

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.02	1.10	D	4.90	4.98	5.10
D <sub>1</sub>	4.80	4.89	5.00	E	6.00	6.11	6.20
E <sub>1</sub>	5.65	5.74	5.85	e	3.72	3.80	3.92
e <sub>1</sub>	--	0.54	--	e <sub>2</sub>	--	1.27	--
f	--	3.82	--	f <sub>1</sub>	0.31	0.37	0.51
f <sub>2</sub>	--	0.64	--	H	--	3.15	--
H <sub>1</sub>	0.59	0.63	0.79	H <sub>2</sub>	0.26	0.28	0.32
L	3.38	3.45	3.58	L <sub>1</sub>	--	1.39	--
v	--	0.13	--	w	0.64	0.68	0.84
y	--	0.34	--		--		--

## Customer Service